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APPLICATION NO.	FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.		CONFIRMATION NO.	
09/681,894		06/21/2001	Roderick A. B. Devine	PR	\$8075	2985	
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KENNTH E CALLAHAN 377 ABW/JAN 2251 MAXWELL SE KIRTLAND AFB, NM 87117 EXAMINER
COLEMAN, WILLIAM D

PAPER NUMBER

ART UNIT

DATE MAILED: 01/02/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

		Ma-
•	Application No.	Applicant(s)
_	09/681,894	DEVINE ET AL.
Office Action Summary	Examiner	Art Unit
	W. David Coleman	2823
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b). Status	I36(a). In no event, however, may a reply be to be sometiment of thirty (30) do will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDON	imely filed ays will be considered timely. m the mailing date of this communication. ED (35 U.S.C. § 133).
1)⊠ Responsive to communication(s) filed on 12	<u>March 2002</u> .	
, .	nis action is non-final.	
Since this application is in condition for allow closed in accordance with the practice under Disposition of Claims	ance except for formal matters, Ex parte Quayle, 1935 C.D. 11,	prosecution as to the merits is 453 O.G. 213.
4) Claim(s) 1-13 is/are pending in the application	n.	
4a) Of the above claim(s) is/are withdra	wn from consideration.	
5) Claim(s) is/are allowed.		
6)⊠ Claim(s) <u>1-13</u> is/are rejected.		
7) Claim(s) is/are objected to.		
8) Claim(s) are subject to restriction and/o	or election requirement.	
Application Papers		
9) The specification is objected to by the Examine		•
10) The drawing(s) filed on is/are: a) acce		
Applicant may not request that any objection to the		
11) The proposed drawing correction filed on		proved by the Examiner.
If approved, corrected drawings are required in re		
12) The oath or declaration is objected to by the E	xaminer.	
Priority under 35 U.S.C. §§ 119 and 120		(a) (d) as (5)
13) Acknowledgment is made of a claim for foreign	gn priority under 35 U.S.C. § 119	(a)-(a) or (f).
a) ☐ All b) ☐ Some * c) ☐ None of:		
1. Certified copies of the priority documer		-C No
2. Certified copies of the priority documer		
 Copies of the certified copies of the pricapplication from the International B See the attached detailed Office action for a lis 	ureau (PCT Rule 17.2(a)).	
14) Acknowledgment is made of a claim for domes	stic priority under 35 U.S.C. § 11	9(e) (to a provisional application).
a) ☐ The translation of the foreign language parts)☐ Acknowledgment is made of a claim for domest	rovisional application has been r	eceived.
Attachment(s)	•	
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 	5) Notice of Inform	ary (PTO-413) Paper No(s) al Patent Application (PTO-152)

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DETAILED ACTION

Response to Arguments

1. Applicant's arguments with respect to claims 1-13 have been considered but are moot in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 103

- 2. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 3. Claims 1-5 and 7-13 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kizilyalli et al., "Deuterium Post-Metal Annealing of MOSFET's for Improved Hot Carrier Reliability", IEEE Electron Device Letters, vol. 18, No. 3, March 1997, pp. 81-83 in view of Gary et al., U.S. Patent 6,328,801 B1.
- 4. Pertaining to claims 1, 7, 11, 12 and 13, <u>Kizilyalli</u> discloses a semiconductor process substantially as claimed. See Abstract where <u>Kizilyalli</u> teaches a silicon-based microcircuit radiation hardening method comprised of:

heating the microcircuit in a furnace to remove any hydrogen in the microcircuit structure; and

annealing the microcircuit with deuterium containing forming gas. However, <u>Kizilyalli</u> fails to teach annealing in a vacuum furnace. <u>Gary</u> teaches a semiconductor process of annealing semiconductor devices in a vacuum furnace. In view of <u>Gary</u>, it would have been obvious to one of ordinary skill in the art to incorporate the vacuum furnace of <u>Gary</u> into the <u>Kizilyalli</u>

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semiconductor process because the invention makes the use of deuterium in the mass production of semiconductor devices, commercially feasible (Abstract of Gary, last sentence).

5. Pertaining to claims 2, 3, 4, 5, 8, 9, 10, 11, given the teaching of the references, it would have been obvious to determine the optimum thickness, temperature as well as condition of delivery of the layers involved. See *In re Aller, Lacey and Hall* (10 USPQ 233-237) "It is not inventive to discover optimum or workable ranges by routine experimentation. Note that the specification contains no disclosure of either the critical nature of the claimed ranges or any unexpected results arising therefrom. Where patentability is said to be based upon particular chosen dimensions or upon another variable recited in a claim, the Applicant must show that the chosen dimensions are critical. *In re Woodruff*, 919 f.2d 1575, 1578, 16 USPQ2d 1934, 1936 (Fed. Cir. 1990).

Any differences in the claimed invention and the prior art may be expected to result in some differences in properties. The issue is whether the properties differ to such an extent that the difference is really unexpected. *In re Merck & Co.*, 800 F.2d 1091, 231 USPQ 375 (Fed. Cir. 1986)

Appellants have the burden of explaining the data in any declaration they proffer as evidence of non-obviousness. *Ex parte Ishizaka*, 24 USPQ2d 1621, 1624 (Bd. Pat. App. & Inter. 1992).

An Affidavit or declaration under 37 CFR 1.132 must compare the claimed subject matter with the closest prior art to be effective to rebut a prima facie case of obviousness. *In re Burckel*, 592 F.2d 1175, 201 USPQ 67 (CCPA 1979).

6. Claim 6 is rejected under 35 U.S.C. 103(a) as being unpatentable over Kizilyalli et al., "Deuterium Post-Metal Annealing of MOSFET's for Improved Hot Carrier Reliability", IEEE Electron Device Letters, vol. 18, No. 3, March 1997, pp. 81-83 in view of Gary et al., U.S. Patent

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6,328,801 B1 as applied to claims 1, 7, 11, 12 and 13 above, and further in view of Warren et al., U.S. Patent 6,159,829.

7. The combined teachings of <u>Kizilyalli</u> and <u>Gary</u> discloses a semiconductor process substantially as claimed. However, the combined teachings fail to disclose wherein the microcircuit includes EEPROM devices. <u>Warren</u> teaches fabricating EEPROM devices. In view of Warren, it would have obvious to one of ordinary skill in the art to incorporate the EEPROM of Warren into the combined teachings of <u>Kizilyalli</u> and Gary because the process can be utilized in a non-volatile NVFET memory device (column 5, lines 4-58).

Conclusion

8. Any inquiry concerning this communication or earlier communications from the examiner should be directed to W. David Coleman whose telephone number is 703-305-0004. The examiner can normally be reached on 9:00 AM-5:00 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 703-306-2794. The fax phone numbers for the organization where this application or proceeding is assigned are 703-308-7722 for regular communications and 703-308-7721 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703-308-0956.

W. David Coleman

Examiner

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WDC December 27, 2002